

# Band switching diode

## 1SS356

### ●Applications

High frequency switching

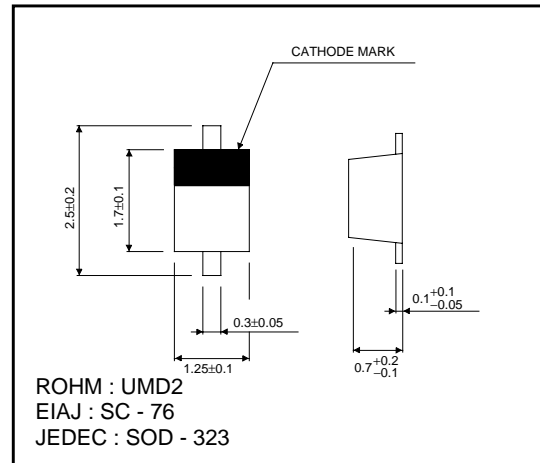
### ●Features

- 1) Small surface mounting type. (UMD2)
- 2) High reliability.

### ●Construction

Silicon epitaxial planar

### ●External dimensions (Units : mm)



### ●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
DC reverse voltage	$V_R$	35	V
DC forward current	$I_F$	100	mA
Junction temperature	$T_j$	125	°C
Storage temperature	$T_{stg}$	-55~+125	°C

### ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_F$	-	-	1.0	V	$I_F=10\text{mA}$
Reverse current	$I_R$	-	-	10	nA	$V_R=25\text{V}$
Capacitance between terminals	$C_T$	-	-	1.2	pF	$V_R=6\text{V}$ , $f=1\text{MHz}$
Forward operating resistance	$r_F$	-	-	0.9	$\Omega$	$I_F=2\text{mA}$ , $f=100\text{MHz}$

Diodes

●Electrical characteristic curves (Ta=25°C)

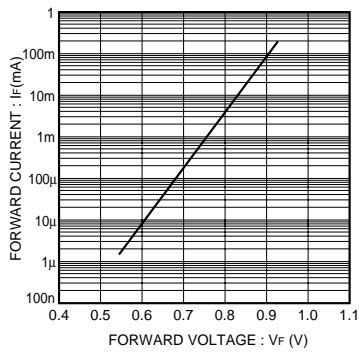


Fig. 1 Forward characteristics

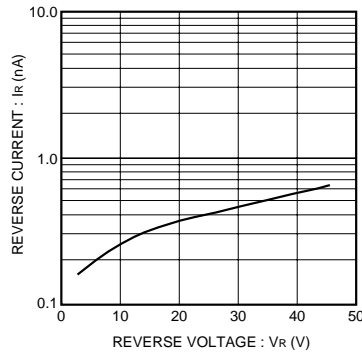


Fig. 2 Reverse characteristics

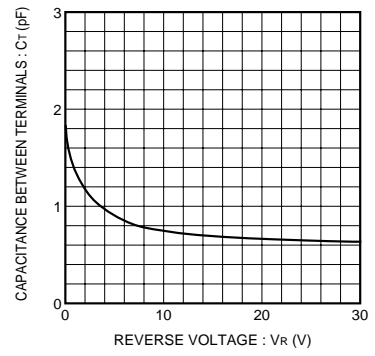


Fig. 3 Capacitance between terminals characteristics

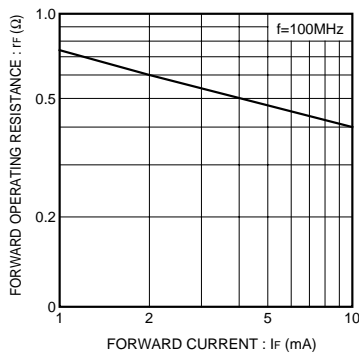


Fig. 4 Forward operating resistance characteristics